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- (10) ((((finfet fin adj2 (fet mosfet mos transistor))[
- (9296036) contact plug interconnect$4 connect$4 via
- (43676) (contact plug interconnect$4 connect$4 via) near6 ((bl bitline bit adj line rea
- (23) ((contact plug interconnect$4 connect$4 via) near6 ((bl bitline bit adj line readlin
- (4) (((contact plug interconnect$4 connect$4 via) near6 ((bl bitline bit adj line readlin
- (894236) gate
- (526070) nm nanometer nano adj meter angstrom
- (24) (((finfet fin adj2 (fet mosfet mos transistor))[
- (22) ((((finfet fin adj2 (fet mosfet mos transistor))[
- (17) ((((finfet fin adj2 (fet mosfet mos transistor))[
- (2) "20040099885"
- (1) ("20040099885" and (nm nanometer nano adj meter angstrom[ )
- (569848) nm nanometer nano adj meter angstrom ang
- (1) ("20040099885" and (nm nanometer nano adj meter angstrom ang[ )
- (164) ((finfet fin adj2 (fet mosfet mos transistor))[
- (1) ("20030102518" and (nm nanometer nano adj meter angstrom ang[ )
- (4) 10/063330
- (4) 10/063330 and (nm nanometer nano adj meter angstrom ang[ )
- (0) "20030102518" and ((wordline "WL" ((word digit control adj gate) adj line) (word
- (2) "20030102518"

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DBs   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB   ☑ Plurals

Default operator: OR   ☑ Highlight all hit terms initially

(((((finfet fin adj2 (fet mosfet mos transistor))
) and ((SRAM static adj3 memory static adj RAM)
)) ((((contact plug interconnect$4 connect$4 via) near6 ((bl bitline bit adj line readline read adj line sense adj line)
)) with ((((finfet fin adj2 (fet mosfet mos transistor))
) fin)) and ((finfet fin adj2 (fet mosfet mos transistor))
))) and gate) and (nm nanometer nano adj meter angstrom
)

#	+r	Inventor	Document I	Issue	P	Title	Current	Current XR	Retrieval	S	C	P				Image Doc.	P
1	☐	☐	Yeo, Yee-Chia	US 2004009	20040	1	CMOS SRAM cell configured using multiple-g	257/208			☑	☐	☑	☑	☐	☐	☐	US 200400	☑
2	☐	☐	Fried, David	US 2003010	20030	2	Finfet SRAM cell using low mobility plane fo	257/401	257/350;		☑	☐	☐	☑	☐	☐	☐	US 200301	☐
3	☐	☐	Nowak, Edw	US 6794718	20040	1	High mobility crystalline planes in double-gat	257/347	438/149;		☑	☐	☐	☑	☐	☐	☐	US 679471	☐
4	☐	☐	Fried, David	US 6664592	20031	1	Fin memory cell and method of fabrication	257/308	257/310;		☑	☐	☑	☑	☐	☐	☐	US 666459	☑
5	☑	☐	Hill, Wiley Eu	US 6787406	20040	2	Systems and methods for forming dense n-ch	438/164	438/302;		☐	☐	☐	☐	☑	☐	☐	US 678740	☐
6	☑	☐	Krivokapic, Z	US 6765303	20040	1	FinFET-based SRAM cell		257/25;		☐	☐	☐	☐	☑	☐	☐	US 676530	☐
7	☑	☐	Grupp, Daniel	US 2004014	20040	1	Insulated gate field effect transistor having p	438/197	438/151;		☐	☐	☐	☐	☐	☐	☐	US 200401	☐
8	☑	☐	Nowak, Edw	US 2004011	20040	1	DENSE DUAL-PLANE DEVICES	257/204	257/206;		☐	☐	☐	☐	☐	☐	☐	US 200401	☐
9	☑	☐	Grupp, Daniel	US 2004002	20040	1	Insulated gate field effect transistor having p	257/330	257/E21.35		☐	☐	☐	☐	☐	☐	☐	US 200400	☐
10	☑	☐	Fried, David	US 2003019	20031	1	FIN MEMORY CELL AND METHOD OF FABRI	257/200			☐	☐	☐	☐	☐	☐	☐	US 200301	☐

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